



40V Dual N-Channel Enhancement Mode MOSFET

Voltage

40 V

Current

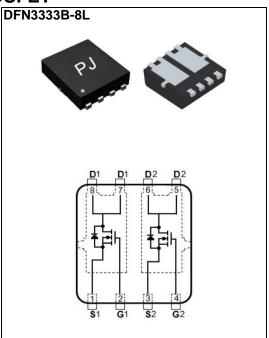
37 A

Features

- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@8A<15m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@6A<20m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultralow on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: DFN3333B-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.001 ounces, 0.027 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	40	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20		
Continuous Drain Current	T _C =25°C	- I _D -	37	А	
	T _C =100°C		23		
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	120		
Power Dissipation	T _C =25°C	Po	33	W	
	T _C =100°C		13	VV	
Continuous Drain Current	T _A =25°C	I _D	9		
	T _A =70°C		7	A	
Power Dissipation	T _A =25°C	Po	2.0	10/	
	T _A =70°C		1.3	W	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	3.79	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	40	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.0	1.75	2.5			
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =8A	-	12.5	15	mΩ		
		V _{GS} =4.5V,I _D =6A	-	15.5	20			
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =40V, V_{GS} =0V	-	-	1.0	uA		
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA		
Dynamic (Note 6)								
Total Gate Charge	Q_g	V _{DS} =20V, I _D =10A, V _{GS} =4.5V ^(Note 2,3)	-	10	-	nC		
Gate-Source Charge	Q_gs		-	3.5	-			
Gate-Drain Charge	Q_gd	V _{GS} =4.5 V	-	3.6	-			
Input Capacitance	Ciss	V 20V V 0V	-	1040	-	pF		
Output Capacitance	Coss	V _{DS} =20V, V _{GS} =0V,	-	117	-			
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	84	-			
Turn-On Delay Time	td _(on)	V_{DS} =20V, I_{D} =1A,	-	9.4	-			
Turn-On Rise Time	t _r	V_{GS} =10V, R_{G} =6 Ω	-	19	-	ns		
Turn-Off Delay Time	td _(off)	(Note 2,3)	-	66	-			
Turn-Off Fall Time	t _f		-	67	-			
Drain-Source Diode								
Maximum Continuous Drain-Source	,				37	Α		
Diode Forward Current	I _S		-	-	31	Α		
Diode Forward Voltage	V _{SD}	I _S =1A,V _{GS} =0V	-	0.7	1	V		

NOTES:

- Pulse width
 2300us, Duty cycle
 2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

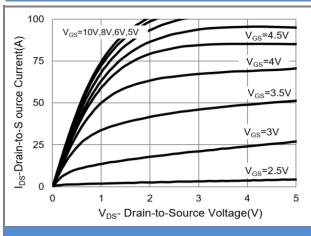


Fig.1 On-Region Characteristics

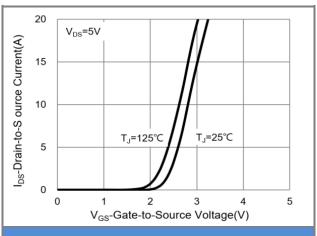


Fig.2 Transfer Characteristics

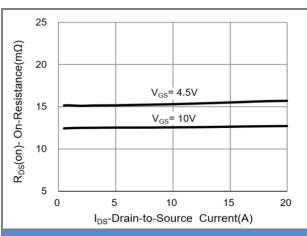


Fig.3 On-Resistance vs. Drain Current

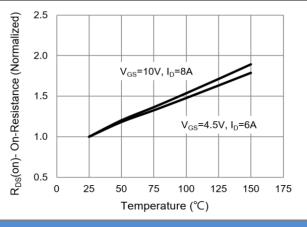


Fig.4 On-Resistance vs. Junction temperature

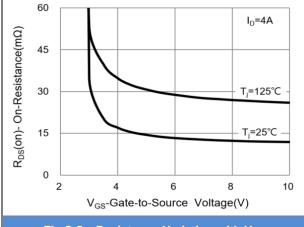
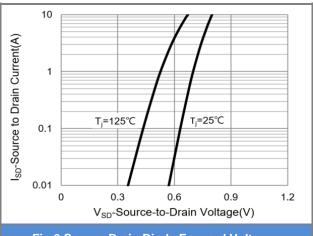


Fig.5 On-Resistance Variation with V_{GS}







TYPICAL CHARACTERISTIC CURVES

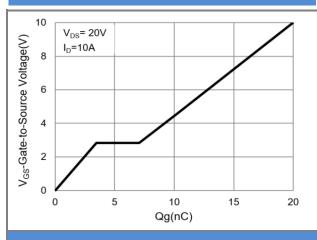


Fig.7 Gate-Charge Characteristics

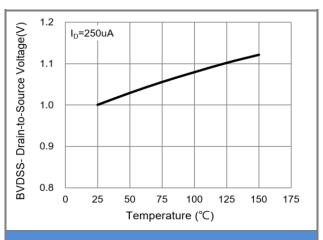


Fig.8 Breakdown Voltage Variation vs. Temperature

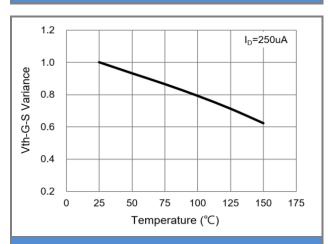


Fig.9 Threshold Voltage Variation with Temperature

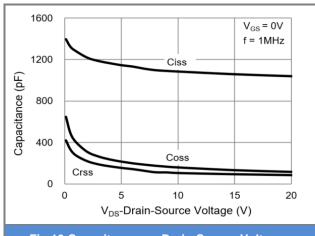
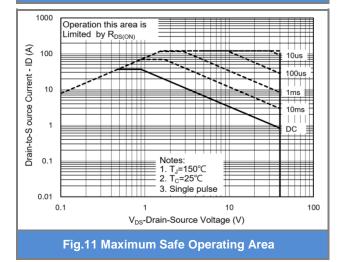


Fig.10 Capacitance vs. Drain-Source Voltage



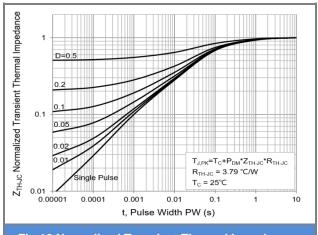


Fig.12 Normalized Transient Thermal Impedance

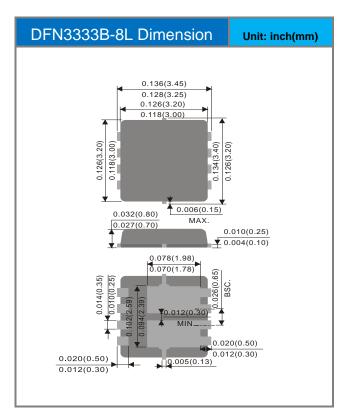


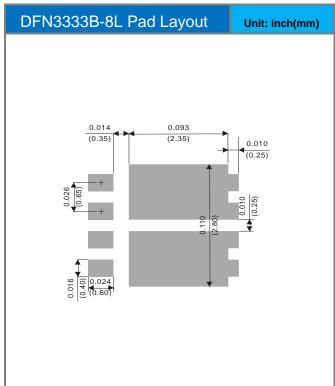


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ4848P_R2_00001	DFN3333B-8L	5K pcs / 13" reel	4848	Halogen free	

Packaging Information & Mounting Pad Layout









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